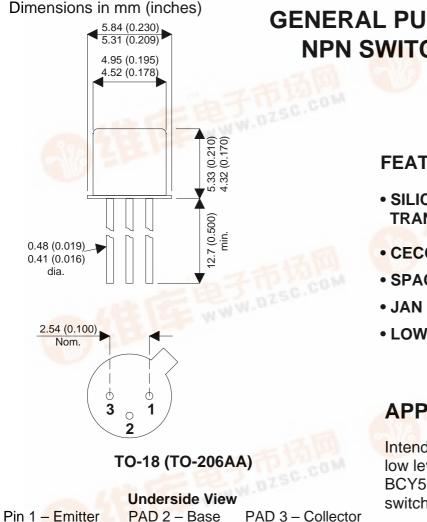
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BCY56



MECHANICAL DATA



GENERAL PURPOSE, LOW POWER, NPN SWITCHING TRANSISTOR

FEATURES

- SILICON PLANAR EPITAXIAL NPN
 TRANSISTOR
- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS
- JAN LEVEL SCREENING OPTIONS
- LOW NOISE

APPLICATIONS:

Intended for general purpose very high gain low level and low noise applications. The BCY56 is also suitable for low speed switching applications.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V _{CBO}	Collector - Base Voltage (I _E =0)	45V		
V _{CEO}	Collector - Emitter Voltage (I _B =0)	45V		
I _C	Collector Current	100mA		
P _{TOT}	Total Power Dissipation T _{amb} < 25°C	300mW		
Т _Ј , Т _{ЅТС}	Maximum Junction And Storage Temperature	-65°C to 175°C		
R _{JC}	Thermal Resistance Junction to Case	200°C/mW		
R ja	Thermal Resistance Junction to Ambient	500°C/mW		

Semelab Pto reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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BCY56

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _E =0	I _C =10μΑ	45	- 71		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _B =0	I _C =10mA	45			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _C =0	I _E =10μΑ	5			-
I _{CBO}	Collector Cut-off Current	I _E =0	V _{CB} =20V			100	nA
I _{EBO}	Emitter Cut-off Current	I _C =0	V _{EB} =5V			100	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C =2mA	V _{CE} =5V	600	650	700	
V _{CE(sat)}	Base-Emitter Saturation Voltage	I _C =10mA	I _B =1mA		80		mV
		I _C =100mA	I _B =10mA		200		
h _{FE}	DC Current Gain	I _C =10μΑ	V _{CE} =5V	40			
		I _C =2mA	V _{CE} =5V	100	200	450	
		I _C =10mA	V _{CE} =5V	100			
f _T	Transition Frequency	I _C =0.5mA	V _{CE} =5V		85		
		I _C =10mA	V _{CE} =5V		250		MHz
C _{CBO}	Collector Capacitance	I _E =0	V _{CB} =5V		4.5		pF
		f=1kHz					
NF	Noise Figure	I _C =200μΑ	V _{CE} =5V		1.5	5	dB
		R _S =2K	f=15kHz				

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